Reliability Qualification Report

SGA-5263Z

Products Qualified by Similarity

SGA-4563Z/4463Z/4363Z/4263Z/4163Z
SGA-3563Z/3463Z/3363Z/3263Z
SGA-2463Z/2363Z/2263Z/2163Z
SGA-1263Z/1163Z
SGA-0363Z/0163Z
SGA-8343Z/8543Z
SGC-2363Z/2463Z/4363Z/4463Z
SGL-0163Z/0263Z/0363Z

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I. Qualification Overview

The SGA-5263Z family of products has demonstrated reliable operation by passing all qualification testing in our product qualification test plan. The “Z’ designates a lead-free lead frame using Tin plated leads and Green mold compound. The SGA-5263Z has been subject to stresses such as humidity (autoclave), extreme hot and cold environments (temperature cycling), moisture sensitivity (MSL-1 and solder reflow testing), and has demonstrated reliable performance.

II. Introduction

Sirenza Microdevices’ SGA-5263Z is a high performance cascadeable 50-ohm amplifier designed for operation at voltages as low as 3.4V. This RFIC uses the latest Silicon Germanium Heterostructure Bipolar Transistor (SiGe HBT) process featuring 1 micron emitters with F_T up to 50GHz. This circuit uses a Darlington pair topology with resistive feedback for broadband performance as well as stability over its entire temperature range. Internally matched to 50 Ohm impedance, the SGA-5263Z requires only DC blocking and bypass capacitors for external components.

III. Fabrication Technology

These amplifiers are manufactured using a Silicon Germanium Heterojunction Bipolar Transistor (HBT) technology. This self-aligned emitter, double poly HBT process has been in production by our foundry since 1998. The process has been successfully used for a wide range of RFIC products including GSM PAs, DECT front end transceivers, LNAs & VCOs. This process offers comparable performance to GaAs HBTs with the added advantages of mature and high producible Silicon wafer processing.

IV. Package Type

The SGA-5263Z power amplifier is packaged in a plastic encapsulated SOT-363 package that is assembled using a highly reproducible automated assembly process. The die is mounted using an industry standard thermally and electrically conductive silver epoxy. The SOT-363 is a similar package differing only by having two more leads than the SOT-343.

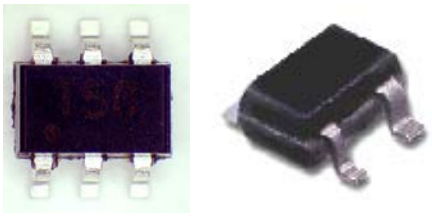

Figure 1: Image of SOT-363 Encapsulated Plastic Package (left) and a SOT-343 Encapsulated Plastic Package (right)

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V. Qualification Methodology

The Sirenza Microdevices qualification process consists of a series of tests designed to stress various potential failure mechanisms. This testing is performed to ensure that Sirenza Microdevices products are robust against potential failure modes that could arise from the various die and package failure mechanisms stressed. The qualification testing is based on JEDEC test methods common to the semiconductor industry. A FMEA approach is used to determine the test methods to be included in the qualification plan. The manufacturing test specifications are used as the PASS/FAIL criteria for initial and final DC/RF tests.

VI. Qualification By Similarity

A device can be qualified by similarity provided that no new potential failure modes/mechanisms are possible in the new design. Products qualified by similarity listed on Page 1 of this document.

VII. Operational Life Testing

Sirenza Microdevices defines operational life testing as a DC biased elevated temperature test performed at the maximum operational junction temperature limit. For the SGA-5263Z the maximum operational temperature limit is 150ºC. The purpose of the operational life test is to statistically show that the product operated at its maximum operational ratings will be reliable by operating several hundred devices for a total time of 1000 hours. The results for this test are expressed in device hours that are calculated by multiplying the total number of devices passing the test by the number of hours tested.

VIII. Moisture Sensitivity Level - MSL Level 1 Device

SGA-5263Z has successfully completed 168 hours of moisture soak (85ºC/85%RH) followed by three convection reflow cycles with a peak temperature of 270ºC. The successful completion of this test classifies the part as JESD 22-A113B Moisture Sensitivity Level 1 (MSL-1). MSL-1 indicates that no special dry pack requirements or time limits from opening of static bag to reflow exist for the SGA-5263Z. MSL-1 is highest level of moisture resistance that a device can be classified according to the above mentioned standard.

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IX. Electrostatic Discharge Classification

Sirenza Microdevices classifies Human Body Model (HBM) electrostatic discharge (ESD) according to the JESD22-A114 convention. All pin pair combinations were tested. Each pin pair is stressed at one static voltage level using 1 positive and 1 negative pulse polarity to determine the weakest pin pair combination. The weakest pin pair is tested with 3 devices below and above the failure voltage to classify the part. The Pass/Fail status of a part is determined by the manufacturing test specification. The ESD class quoted indicates that the device passed exposure to a certain voltage, but does not pass the next higher level. The following table indicates the JESD ESD sensitivity classification levels.

Class	Passes	Fails
0	0 V	<250 V
1A	250 V	500 V
1B	500 V	1000 V
1C	1000 V	2000 V
2	2000 V	4000 V

Part Number	ESD Rating
SGA-2163Z	Class 1B
SGA-3x63Z	Class 1B
SGA-4x63Z	Class 1B
SGA-5263Z	Class 1B
SGA-0163Z	Class 0
SGA-1163Z	Class 0
SGA-8343Z	Class 1A
SGL-0363Z	Class 1B

X. Operational Life Test Results

The results for SGA-5263Z High Temperature Operating Life Test are as follows

HTOL Completion Date	Test Duration	Junction Temperature	Quantity	Device Hours
June-04	**1000 hours**	**150°C**	**80**	**80,000**

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XI. Qualification Test Results

Group	Test Name	Test Condition/ Standard	Sample Size	Results
A0	Preconditioning	MSL1 Reflow @ 270ºC Peak JESD22-A113C	210	Pass
A1a	Temperature Cycling	Air to Air, Soldered on PCB -65ºC to 150ºC 10 min dwell, 1 min transition 1000 cycles JESD22-A104B	20	Pass
A1b	Temperature Cycle	-65°C to +150°C 10 min dwell, 1 min transition 1000 cycles JESD22-A104B	20	Pass
A2	High Temperature Operating Life	Tj = 150°C 1000 hours JESD22-A108B	80	Pass
B	HAST	Tamb=110°C, 85%RH Biased, 264 hours JESD22-A110B	15	Pass
C	Autoclave	Tamb=121°C, 100%RH Un-Biased, 96 hours JESD22-A102C	40	Pass

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VIII. Qualification Test Results

Group	Test Name	Test Condition/ Standard	Sample Size	Results
D	Power Temperature Cycle	-40°C to +85°C Cycled bias (5' on/5'off) 1000 cycles JESD22-A109A	20	Pass
E	High Temperature Storage	Tamb=150°C 1000 hours JESD22-A103B	20	Pass
F	Low Temperature Storage	Tamb=-40°C 1000 hours	20	Pass
I	Tin Whisker	Tamb=51°C, 85%RH 1000 hours	10	Pass
G	Solderability	Dip & Look Sn/Ag/Cu solder Steam Age Condition C Dip Condition B, 245°C JESD22-B102C	15	Pass

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XII. Junction Temperature Determination

One key issue in performing qualification testing is to accurately determine the junction temperature of the device. Sirenza Microdevices uses a 3um spot size emissivity corrected infrared camera measurement to resolve the surface temperature of the device at the maximum operational power dissipation. The results are displayed below for the device running at operational current of 60.9 mA, a device voltage of 3.18 V, and a lead temperature of 87.7°C.

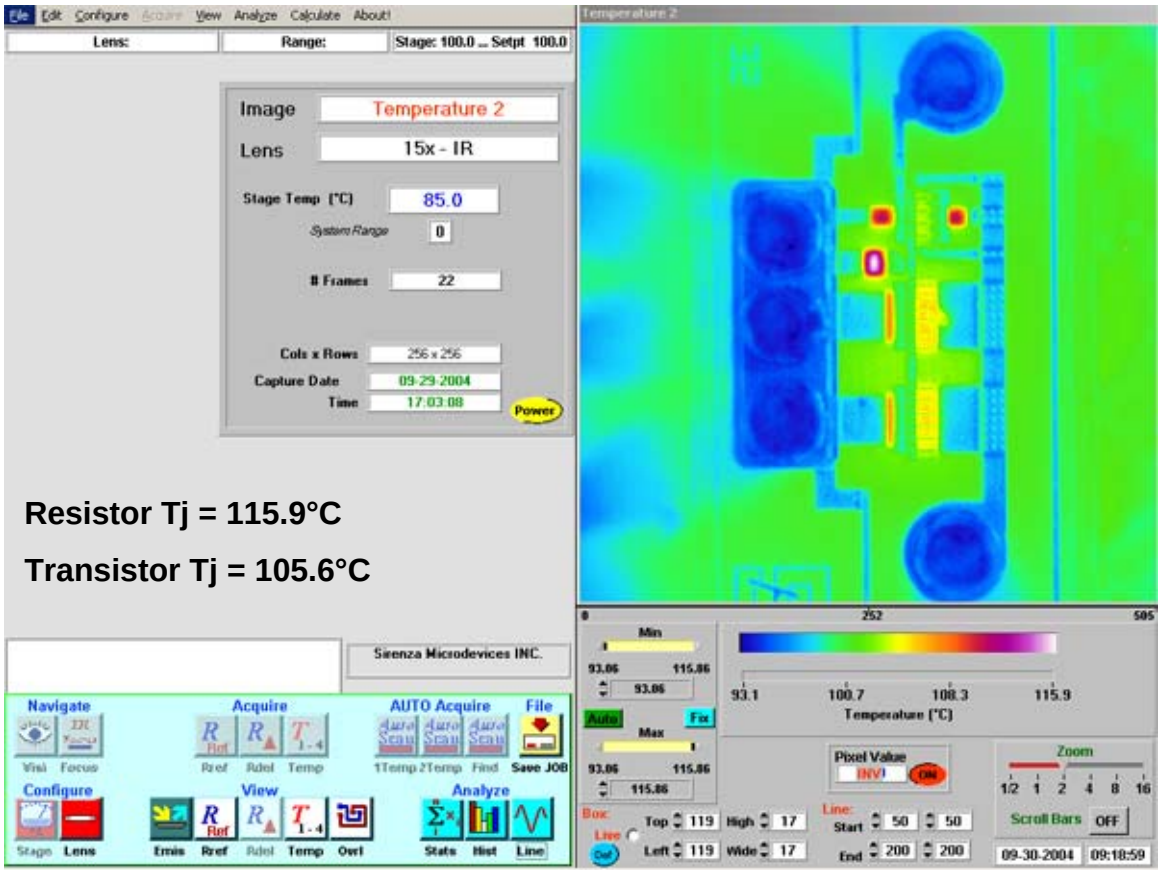

Figure 2: Infrared Thermal Image of SGA-5263Z, Vd =3.18 V, Id =60.9 mA, T lead = 87.7°C

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XIV. Junction Temperature Determination of SGA-8343Z

One key issue in performing qualification testing is to accurately determine the junction temperature of the device. Sirenza Microdevices uses a 3um spot size emissivity corrected infrared camera measurement to resolve the surface temperature of the device at the maximum operational power dissipation. The results are displayed below for the device running at operational current of 50.0mA, a device voltage of 4V, and a lead temperature of 85.1°C.

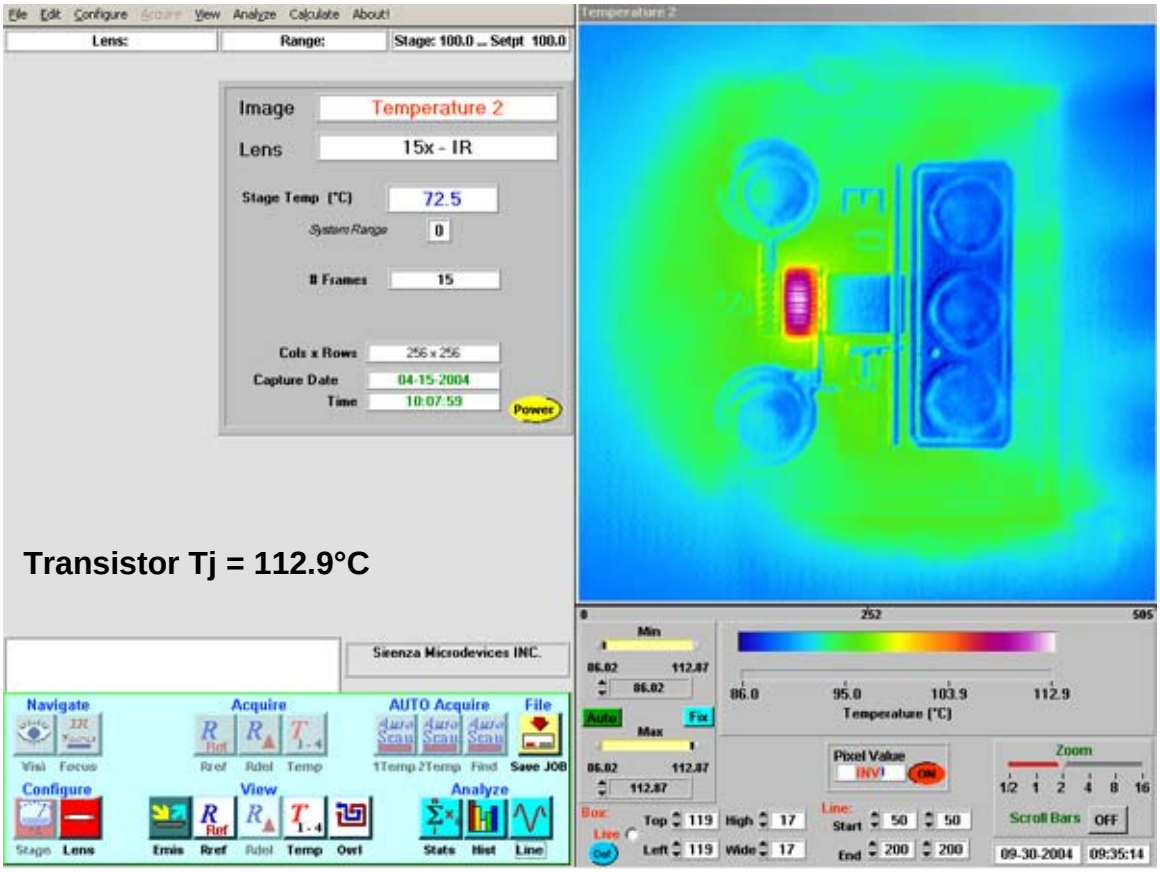

Figure 2: Infrared Thermal Image of SGA-8343Z, Vd =4V, Id =50.0mA, T lead = 85.1°C